

# BUK9608-55B

# N-channel TrenchMOS logic level FET Rev. 04 — 4 May 2010

**Product data sheet** 

### **Product profile**

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
I <sub>D</sub>	drain current	$V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	75	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	203	W
Static char	acteristics						
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;}$ $T_j = 25 \text{ °C}$		-	6.2	7	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{Figure 12}};$ see Figure 12		-	7.1	8.4	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 75 \text{ A}; V_{sup} \le 55 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 5 \text{ V};$ $T_{j(init)} = 25 ^{\circ}\text{C}; \text{ unclamped}$	-	-	352	mJ
Dynamic cl	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 44 \text{ V}; T_j = 25 \text{ °C};$ see Figure 13	-	16	-	nC

<sup>[1]</sup> Continuous current is limited by package.

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain <sup>[1]</sup>	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make a connection to pin 2.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9608-55B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404
BUK9608-55B/C1	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

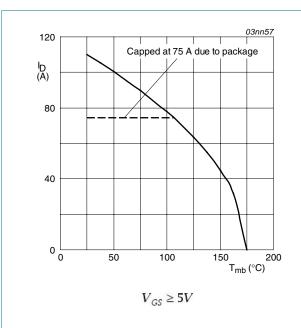
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
$V_{GS}$	gate-source voltage			-15	-	15	V
I <sub>D</sub>	drain current	$T_{mb} = 100  ^{\circ}\text{C};  V_{GS} = 5  \text{V};  \text{see}  \frac{\text{Figure 1}}{}$	<u>[1]</u>	-	-	75	Α
		$T_{mb} = 25  ^{\circ}\text{C};  V_{GS} = 5  \text{V};  \text{see}  \frac{\text{Figure 1}}{\text{Figure 1}};$	[2]	-	-	110	Α
		see Figure 3	[1]	<u>l</u> '	75	Α	
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p$ ≤ 10 μs; pulsed; see Figure 3		-	-	439	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	203	W
T <sub>stg</sub>	storage temperature			-55	-	175	°C
T <sub>j</sub>	junction temperature			-55	-	175	°C
Source-drain	diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[2]	-	-	110	Α
			<u>[1]</u>	-	-	75	Α
I <sub>SM</sub>	peak source current	$t_p \le 10  \mu \text{s}; \text{ pulsed};  T_{mb} = 25  ^{\circ}\text{C}$		-	-	439	Α
Avalanche rug	gedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup}$ ≤ 55 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	352	mJ

<sup>[1]</sup> Continuous current is limited by package.

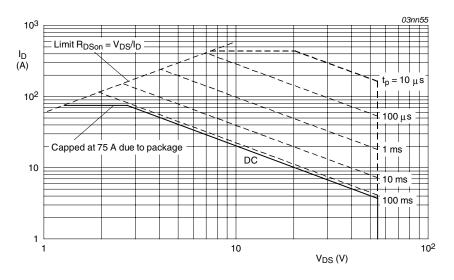
<sup>[2]</sup> Current is limited by power dissipation chip rating.



03na19 120 P<sub>der</sub> (%) 80 40 0 \_ 100 150 200 T<sub>mb</sub> (°C)  $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$ 

Continuous drain current as a function of mounting base temperature

Normalized total power dissipation as a Fig 2. function of mounting base temperature



 $T_{mb} = 25$ °C;  $I_{DM}$ is single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage Fig 3.

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.74	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a PCB	-	50	-	K/W

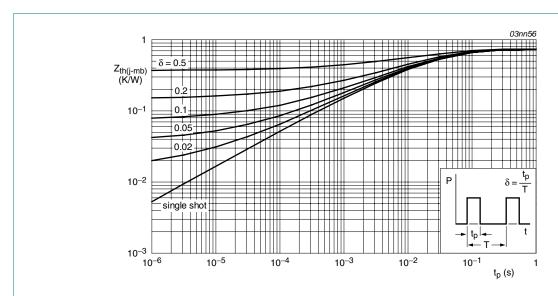


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration

# 6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 10	1.1	1.5	2	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 10	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I <sub>GSS</sub> gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 15 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ	
		$V_{DS} = 0 \text{ V}; V_{GS} = -15 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	9.3	mΩ
resistance	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	16.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	6.2	7	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11; see Figure 12	-	7.1	8.4	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 5 \text{ V};$	-	45	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	9	-	nC
$Q_{GD}$	gate-drain charge		-	16	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	3960	5280	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	517	620	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	206	282	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	29	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	123	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	131	-	ns
t <sub>f</sub>	fall time		-	86	-	ns
L <sub>D</sub>	internal drain inductance	from drain lead 6 mm from package to center of die ; $T_j = 25  ^{\circ}\text{C}$	-	4.5	-	nΗ
		from upper edge of drain mounting base to center of die ; $T_j = 25  ^{\circ}\text{C}$	-	2.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_j = 25~^{\circ}\text{C}$	-	7.5	-	nΗ

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	69	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	72	-	nC

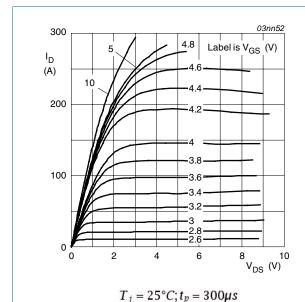


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

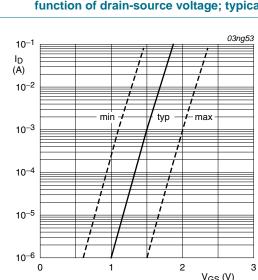
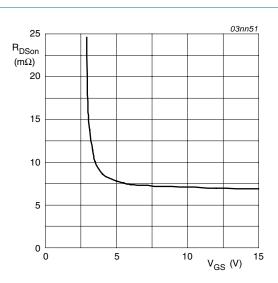


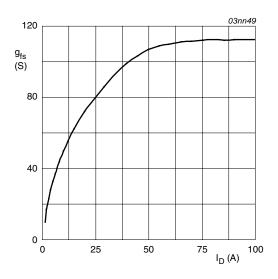
Fig 7. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25 \,{}^{\circ}C; V_{DS} = V_{GS}$ 



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25^{\circ}C; V_{DS} = 25V$ 

Fig 8. Forward transconductance as a function of drain current; typical values

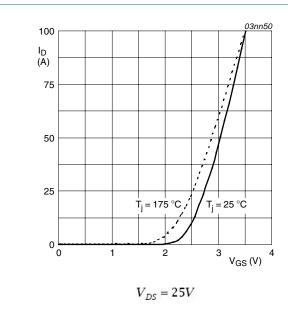


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

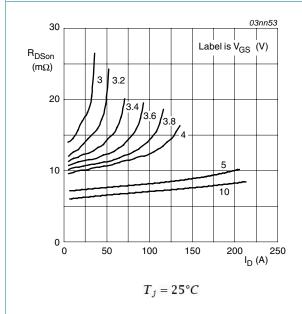
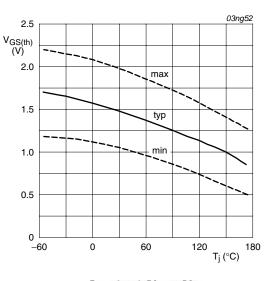


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = \mathbf{1} m A; V_{DS} = V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

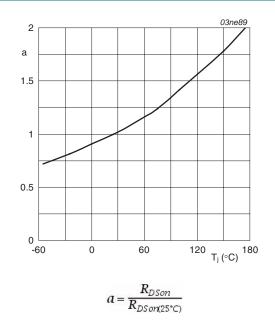


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

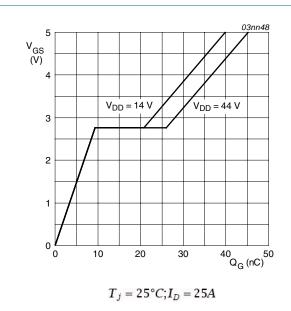
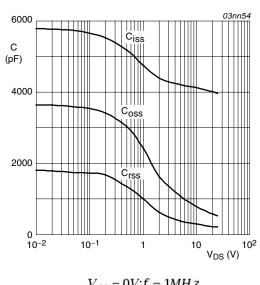


Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

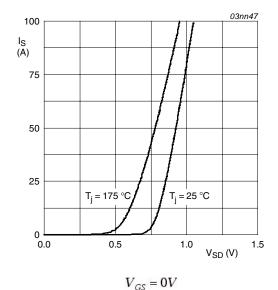


Fig 15. Source current as a function of source-drain voltage; typical values

## 7. Package outline

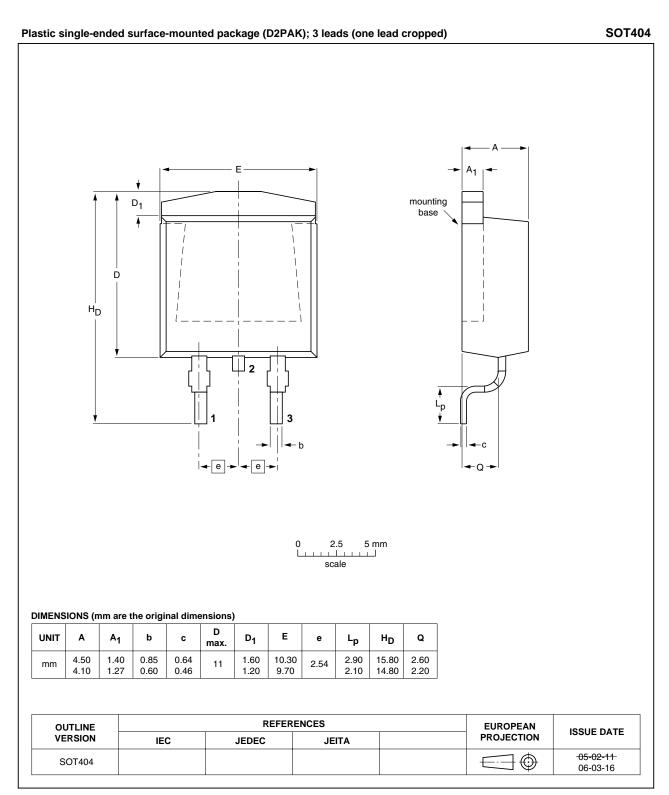


Fig 16. Package outline SOT404 (D2PAK)

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9608-55B_4	20100504	Product data sheet	-	BUK9608-55B_3
Modifications:	<ul> <li>Various cha</li> </ul>	inges to content.		
BUK9608-55B_3	20100429	Product data sheet	-	BUK95_96_9E08_55B-02

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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# BUK9608-55B

## **Nexperia**

N-channel TrenchMOS logic level FET

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